

Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	150.00 +/- 0.50 mm	WaferVendor
	2.0 Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0 Primary Flat Orientation	{110} +/-1 degree	Wafer Vendor
	4.0 Growth Method	CZ	Wafer Vendor
	5.0 Type	Any	Wafer Vendor
	6.0 Dopant	Any	Wafer Vendor
	7.0 Resistivity	0.1~ 100 ohm cm	Wafer Vendor
	8.0 Overall Thickness	380.00 +/- 10.00 um	Wafer Vendor
	9.0 Total Thickness Variation (TTV)	<3.00um	Guaranteed by process
	10.0 Bow	<50.00um	ADE to ASTM F534, 20%
	11.0 Warp	<50.00um	ADE to ASTM F657, 20%
	12.0 Lasermarking	On wafer FRONTSIDE opposite the flat. Scribe format: [ICE-6-380.XXXX] (unique scribe)	Guaranteed by process
	13.0 Orientation	<100> +/-0.5	Wafer Vendor
	14.0 Back Surface Quality	Polished.	Wafer Vendor
	15.0 Front Surface Quality	Prime	Wafer Vendor
	16.0 Edge Chips	None	Bright Light 100% (note 2)
HandleSilicon	17.0 Handle Thickness	380.00 +/- 10.00 um	ADE
	18.0 Surface Haze	None	Bright Light, 100% (note 2).
	19.0 Total scratch length	None	Bright Light, 100% (note 2).

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Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information